

L Number	Hits	Search Text	DB	Time stamp
-	833	438/618	USPAT; EPO; JPO; DERWENT	2003/03/10 10:42
-	672	438/633	USPAT; EPO; JPO; DERWENT	2001/12/17 14:40
-	45384	barrier adj (layer or film)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:06
-	1055	(barrier adj (layer or film)) and (reduc\$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/18 08:16
-	237	((barrier adj (layer or film)) and (reduc\$4 adj (gas or agent or chemical))) and (metal adj (film or layer))	USPAT; EPO; JPO; DERWENT	2001/12/18 08:17
-	5	(barrier adj (layer or film)) and (first adj reduc\$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/17 14:56
-	0	((barrier adj (layer or film)) and (first adj reduc\$4 adj (gas or agent or chemical))) and (metal adj (film or layer))	USPAT; EPO; JPO; DERWENT	2001/12/17 14:53
-	0	((barrier adj (layer or film)) and (reduc\$4 adj (gas or agent or chemical))) and (metal adj (film or layer))) and (second adj reduc\$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/17 14:55
-	237	((barrier adj (layer or film)) and (reduc\$4 adj (gas or agent or chemical))) and (metal adj (film or layer))) and (reduc\$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/17 14:55
-	163	(first adj reduc\$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/17 14:58
-	92	((first adj reduc\$4 adj (gas or agent or chemical))) and (second adj reduc\$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/17 15:01
-	6	((first adj reduc\$4 adj (gas or agent or chemical))) and (second adj reduc\$4 adj (gas or agent or chemical))) and semiconductor	USPAT; EPO; JPO; DERWENT	2001/12/17 15:01
-	683	438/627	USPAT; EPO; JPO; DERWENT	2001/12/17 15:31
-	1178	438/643	USPAT; EPO; JPO; DERWENT	2002/01/02 14:19
-	20851	((diffus\$6 adj barrier) or prevent\$10) adj (layer or film))	USPAT; EPO; JPO; DERWENT	2001/12/18 14:01
-	394	((diffus\$6 adj barrier) or prevent\$10) adj (layer or film))) and (reduc\$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/18 08:17
-	96	((diffus\$6 adj barrier) or prevent\$10) adj (layer or film))) and (reduc\$4 adj (gas or agent or chemical))) and (metal adj (film or layer))	USPAT; EPO; JPO; DERWENT	2001/12/18 12:54
-	20851	((diffus\$6 adj barrier) or prevent\$10) adj (layer or film))	USPAT; EPO; JPO; DERWENT	2001/12/18 14:02
-	3447	((diffus\$6 adj barrier) or (diffus\$6 adj prevent\$10)) adj (layer or film))	USPAT; EPO; JPO; DERWENT	2001/12/18 14:04
-	40	((diffus\$6 adj barrier) or prevent\$10) adj (layer or film)) ) and (first adj anneal\$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:07
-	0	((diffus\$6 adj barrier) or prevent\$10) adj (layer or film)) ) and (first adj anneal\$5)) and (second adj aneal\$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:08

-	45418	barrier adj (layer or film)	USPAT; EPO; JPO; DERWENT	2003/03/07 13:53
-	147	(barrier adj (layer or film) ) and (first adj anneal\$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:08
-	0	((barrier adj (layer or film) ) and (first adj anneal\$5)) and (second adj aneal\$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:21
-	483098	plug or interconnection	USPAT; EPO; JPO; DERWENT	2001/12/18 14:23
-	108014	metal adj (layer or film)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:24
-	18975	(metal adj (layer or film)) and (plug or interconnect\$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:25
-	3544	((metal adj (layer or film)) and (plug or interconnect\$5)) and anneal\$5	USPAT; EPO; JPO; DERWENT	2001/12/18 14:25
-	56	((metal adj (layer or film)) and (plug or interconnect\$5)) and anneal\$5) and (reduc\$3 adj atmosphere)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:30
-	6	((barrier adj (layer or film) ) and (first adj anneal\$5)) and (reduc\$3 adj atmosphere)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:31
-	40	((metal adj (layer or film)) and (plug or interconnect\$5)) and anneal\$5) and (reduc\$3 adj atmosphere)) and semiconductor	USPAT; EPO; JPO; DERWENT	2001/12/18 14:37
-	6	((barrier adj (layer or film) ) and (first adj anneal\$5)) and (reduc\$3 adj atmosphere)) and semiconductor	USPAT; EPO; JPO; DERWENT	2001/12/18 14:36
-	5	((("5116463") or ("6207222") or ("6197688") or ("6191031") or ("6143646")).PN.	USPAT	2002/01/02 14:18
-	562	438/687	USPAT; EPO; JPO; DERWENT	2002/01/02 14:19
-	55733	barrier adj (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/10 07:56
-	489	(barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/07 14:01
-	160	((barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))) and (metal adj (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/07 14:03
-	3	((barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))) and (metal adj (layer or film)) and (second adj (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/07 14:08
-	222	(barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient)) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/07 14:05
-	3	((barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))) and (metal adj (layer or film)) and (second adj (gas or ambient))) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/07 13:59

-	113	((barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))) and (metal adj (layer or film))) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:06
-	28226	(barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:03
-	6490	((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))) and (metal adj (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:05
-	222	((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))) and (reduc\$3 adj (gas or ambient)) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:07
-	8105	((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:07
-	3403	((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))) and (metal adj (layer or film))) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:07
-	99	((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:07
-	99	((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient)) and (second adj (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:10
-	92	((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient)) and (second adj (gas or ambient)) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:10
-	25099	barrier adj (layer or film)	USPAT	2003/03/10 07:56
-	7320	(barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))	USPAT	2003/03/10 08:01
-	3856	((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor	USPAT	2003/03/10 08:02
-	1694	((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film))	USPAT	2003/03/10 08:03
-	303	((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))	USPAT	2003/03/10 08:04
-	60	((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film))) and (second adj gas)	USPAT	2003/03/10 08:05

-	9	(((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas)	USPAT	2003/03/10 08:05
-	2	("5665659" or ("5953634")).PN.	USPAT	2003/03/10 10:42